

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

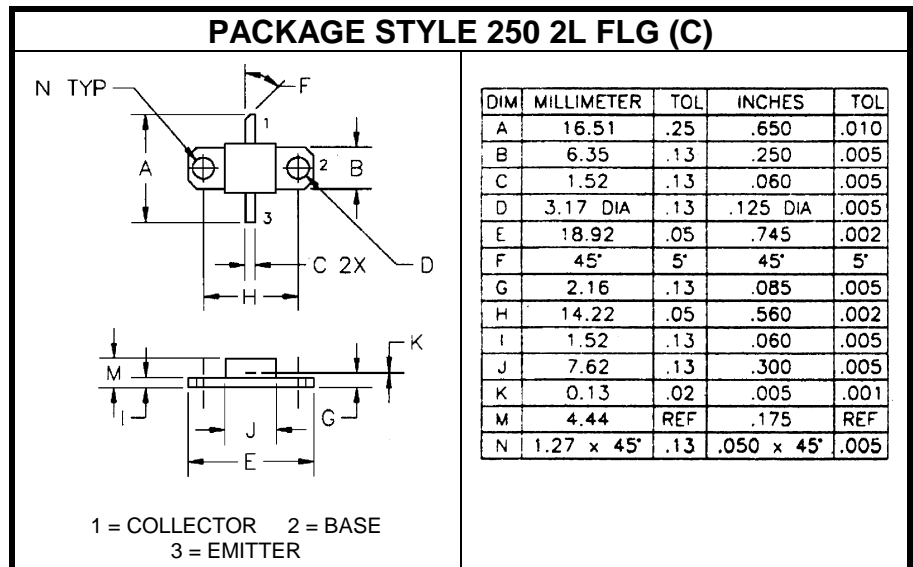
The **MRA1417-11H** is a Common Base Device Designed for Class C Amplifier Applications in L-Band FM Microwave Links.

## FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

## MAXIMUM RATINGS

$I_C$	2.0 A
$V_{CBO}$	50 V
$P_{DISS}$	29 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$\theta_{JC}$	$6.0^\circ\text{C/W}$



## CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 80\text{ mA}$	50			V
$BV_{CES}$	$I_C = 80\text{ mA}$	55			V
$BV_{EBO}$	$I_E = 5.0\text{ mA}$	3.5			V
$h_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 800\text{ mA}$	10			---
$C_{ob}$	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		12		pF
$P_G$ $\eta_c$	$V_{CE} = 28\text{ V}$ $P_{OUT} = 12.0\text{ W}$ $f = 1400 - 1700\text{ MHz}$	7.0	7.5 40		dB %